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(54) **NONVOLATILE MEMORY DEVICE AND METHOD OF FORMING SAME**

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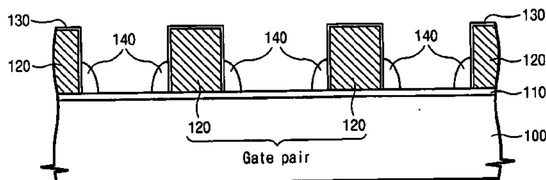
(57) **ABSTRACT**

In a method of forming a silicon-oxide-nitride-oxide-silicon (SONOS) type nonvolatile memory device, a plurality of first gates may be formed on a semiconductor substrate. A plurality of charge storage spacers may be formed on the plurality of first gates so that a given charge storage spacer may be disposed on a sidewall of a given first gate. A plurality of second gates may be disposed on the plurality of first gates so that a given second gate is on a sidewall of a given first gate and covers a given charge storage spacer.



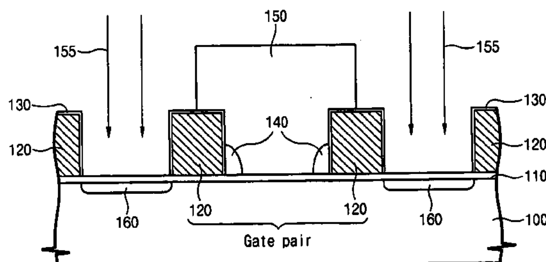


Fig. 1A

185 140 120 225 202 220 202 I' R 120 140 185 204 105 105 105 185 Ref 140 120 225 202 220 202 L I 120 140 225 185

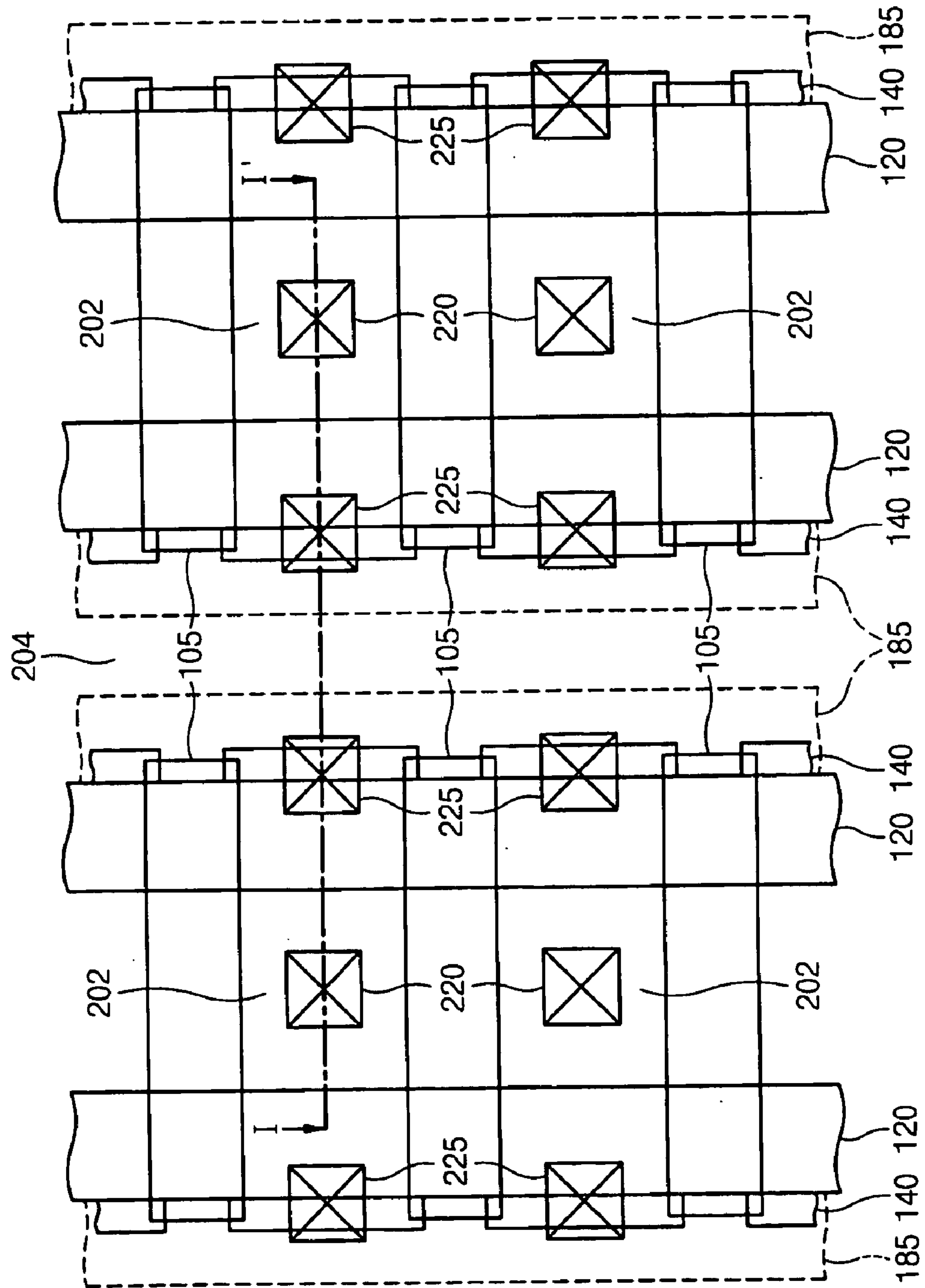


Fig. 1B
185
140
120
225
I'
202
220
105
204
I

Fig. 1B

Fig. 1C

185 140 120 140 202 220 225 105 204

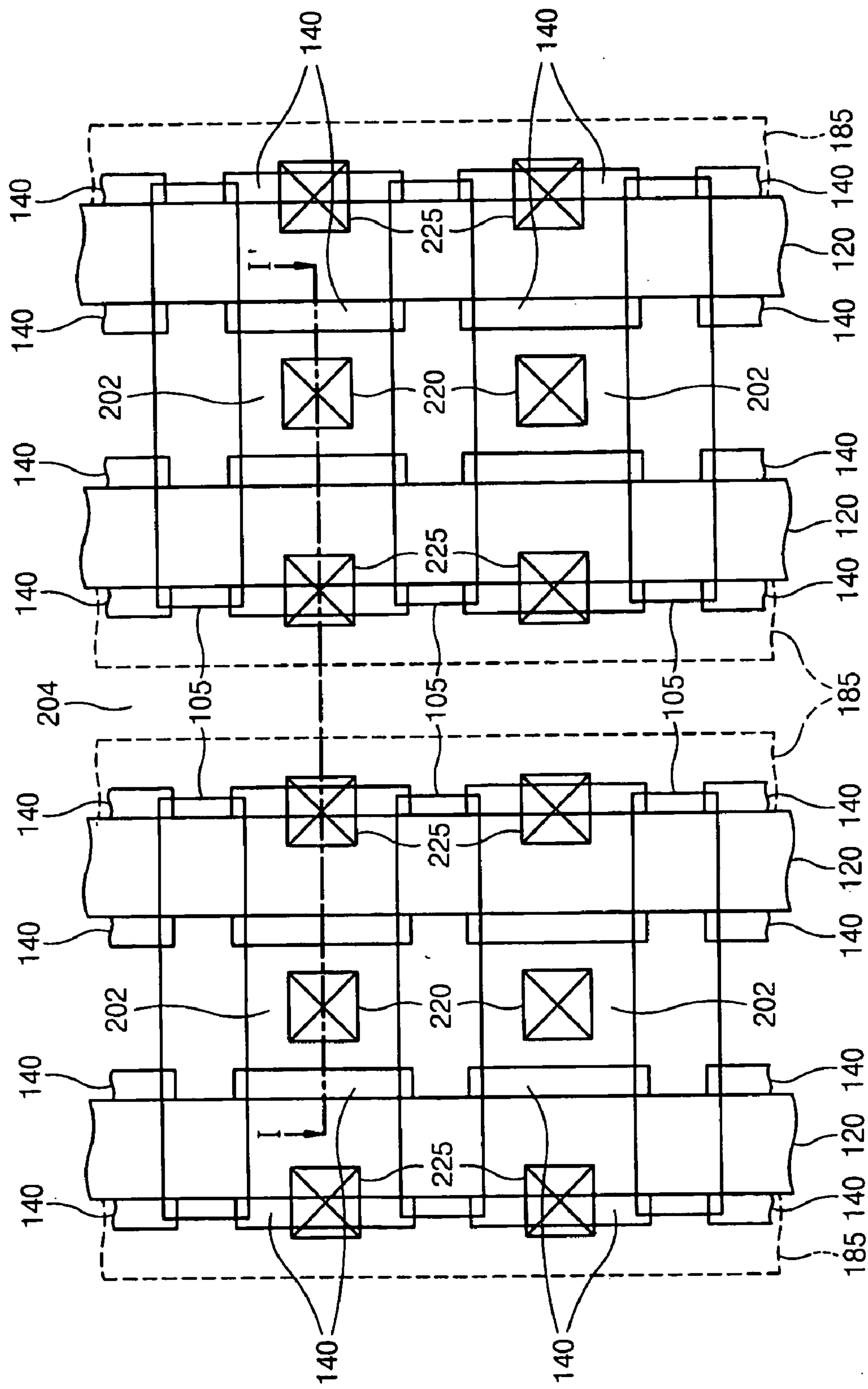


Fig. 1D
140
185
225
120
202
220
105
204
I
I'

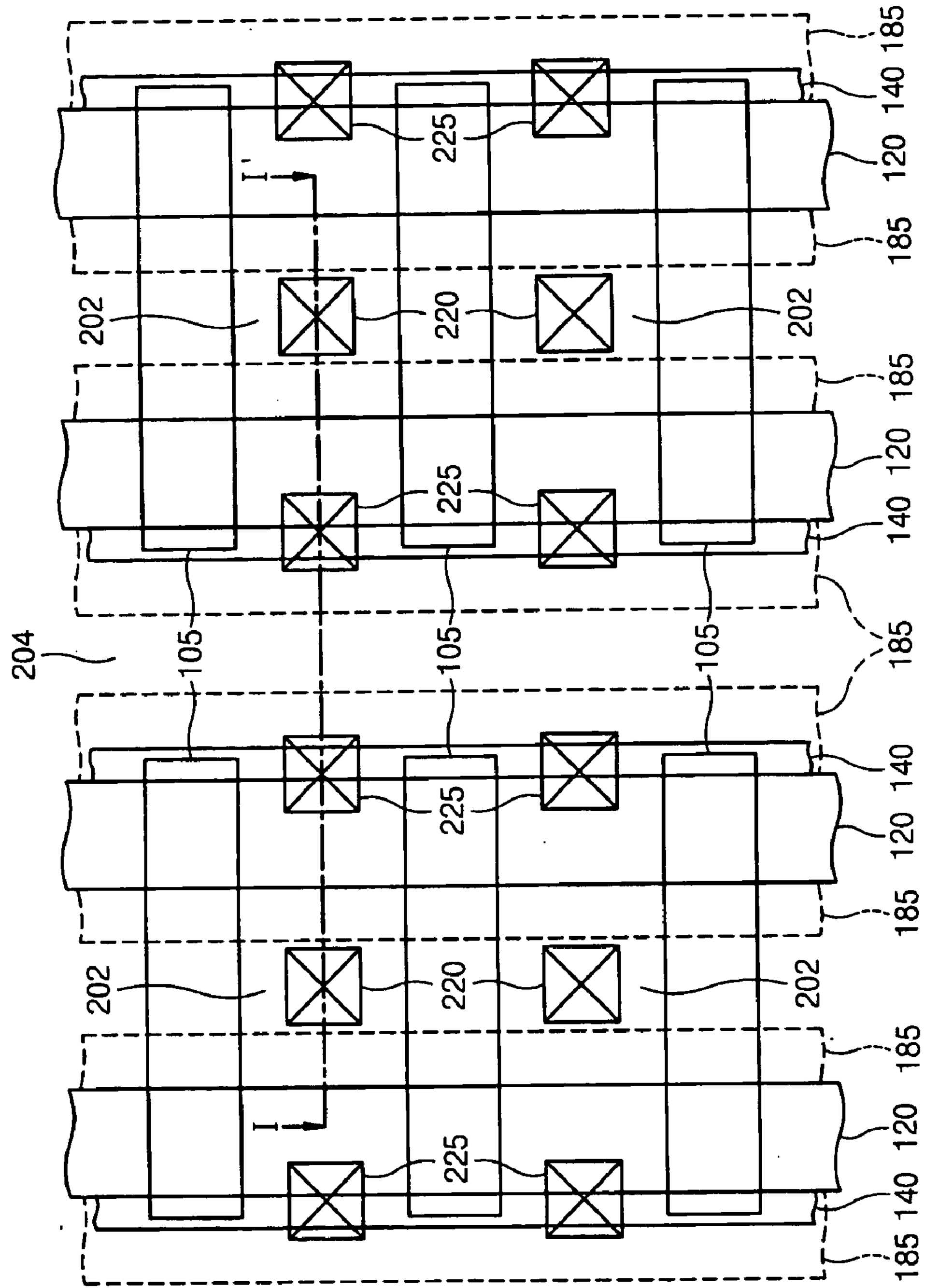
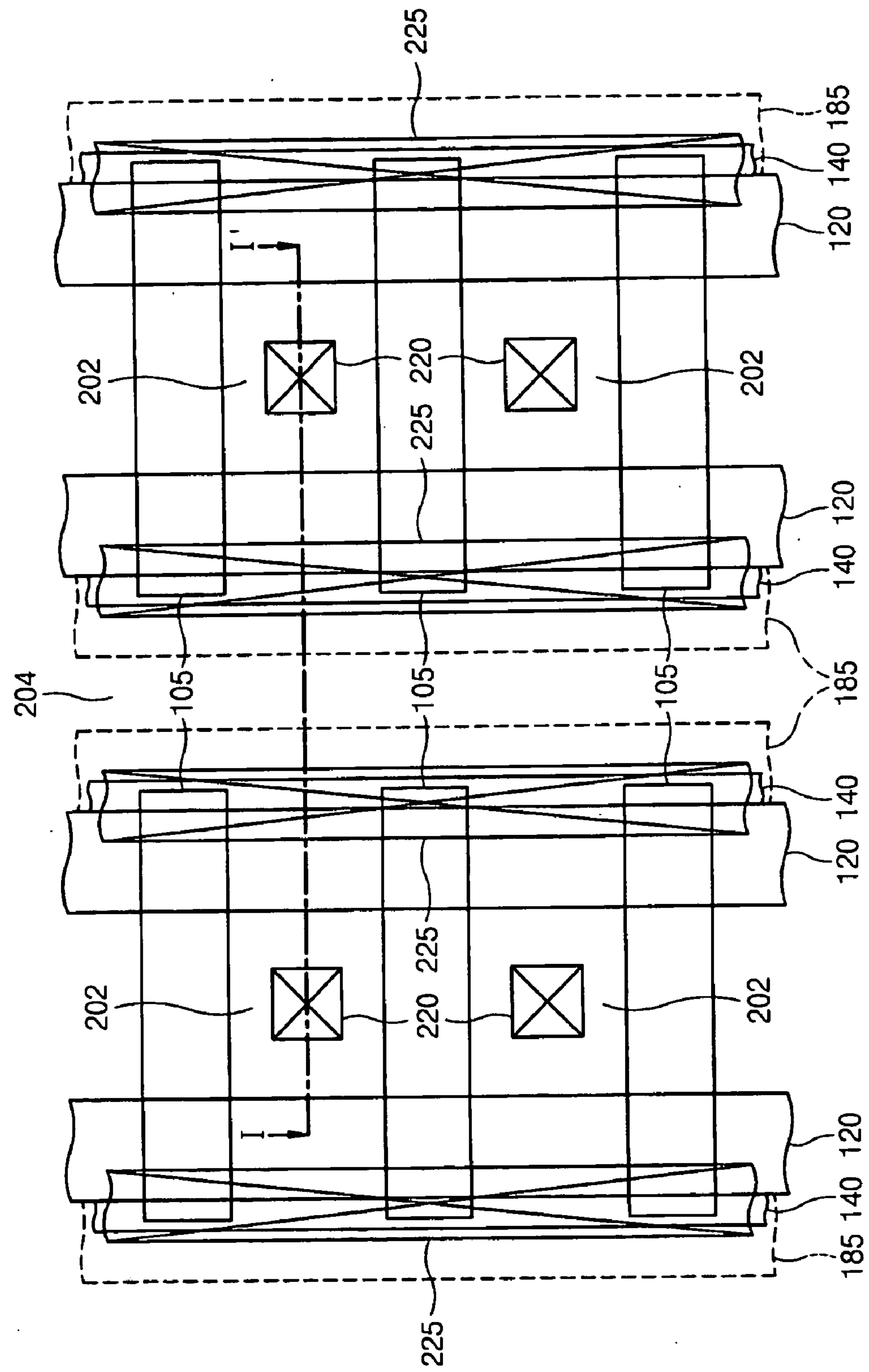


Fig. 1E
185
140
120
225
202
220
105
204
I
I'

Fig. 1F



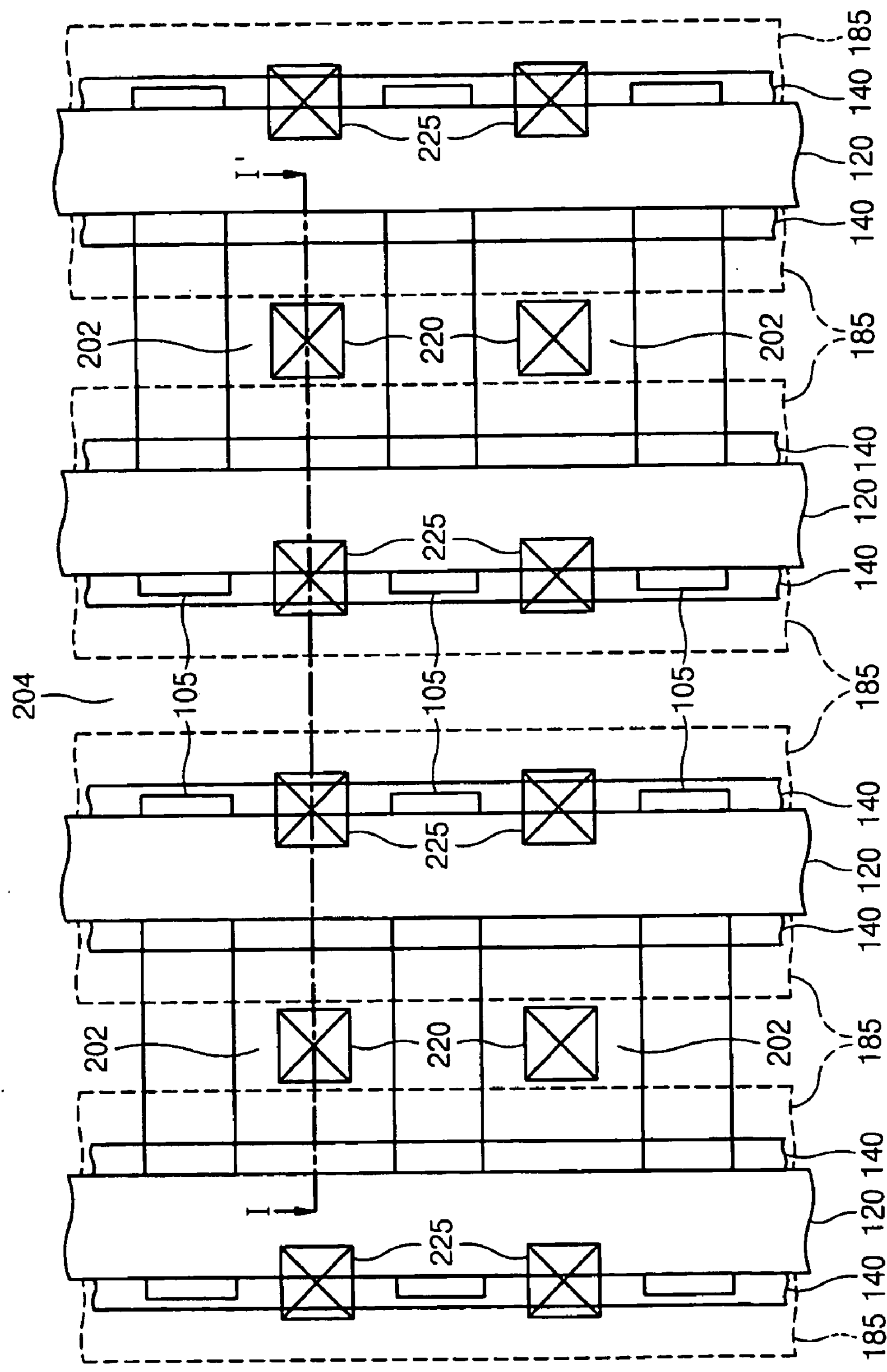


Fig. 1G
185
140
120
140
225
202
220
202
185
140
120
140
225
105
204
185
I'
I

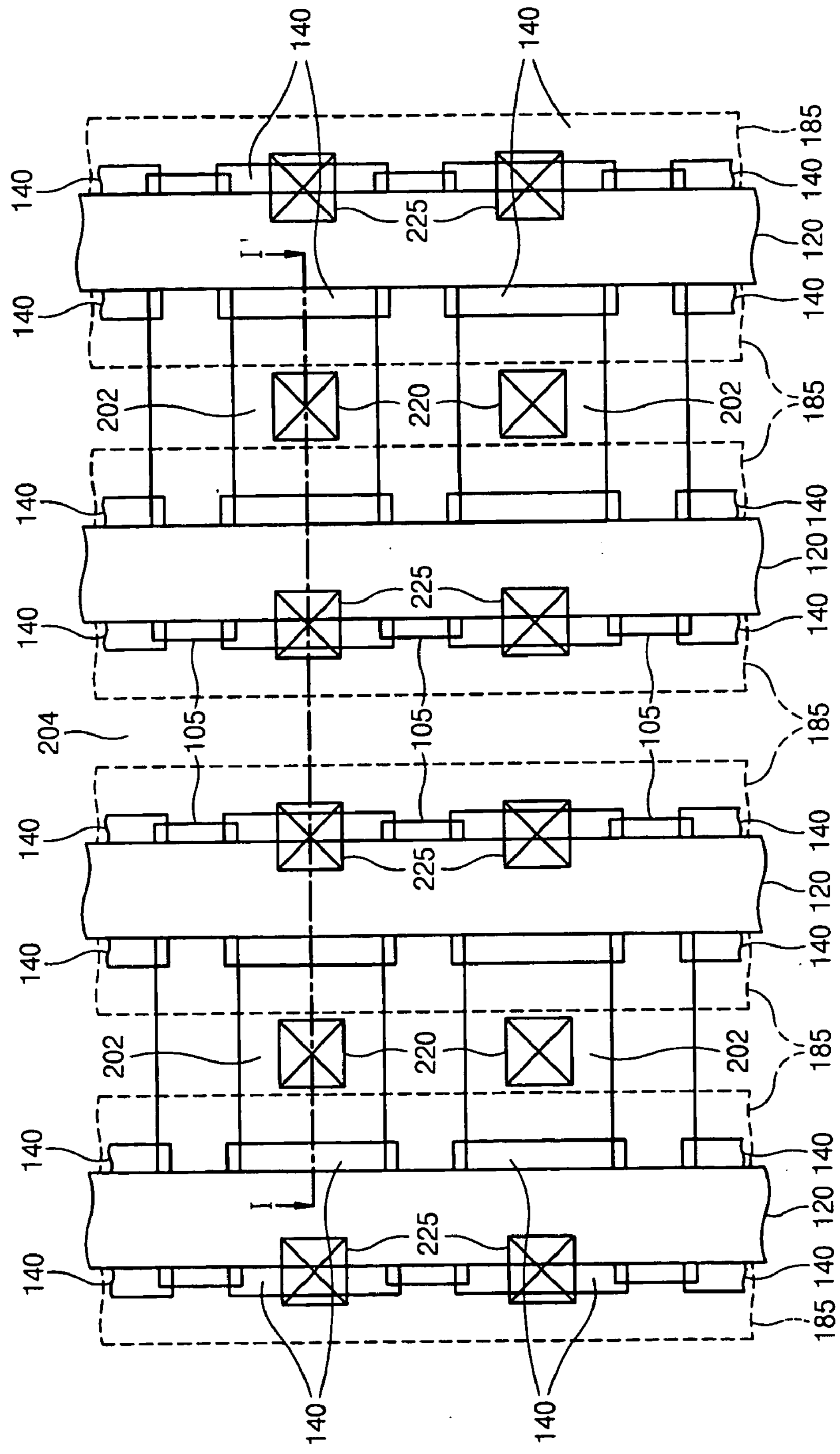


Fig. 1H

Fig. 2A

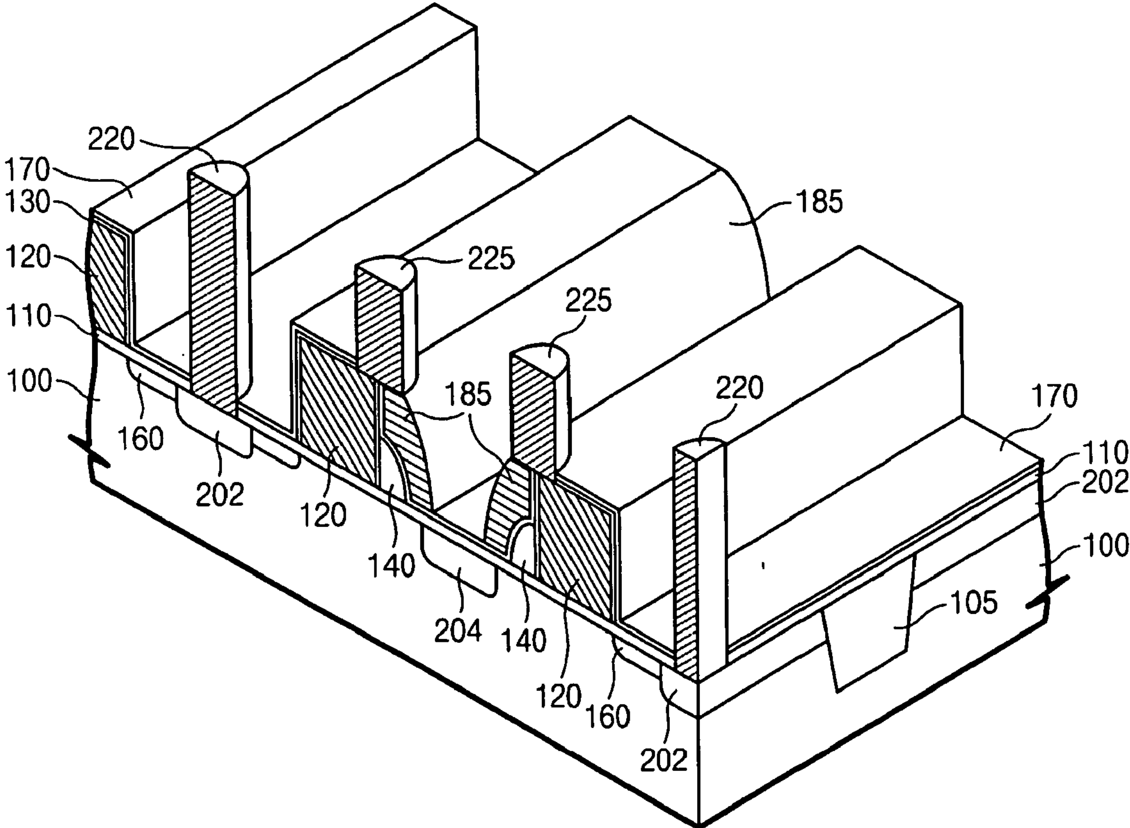


Fig. 2B

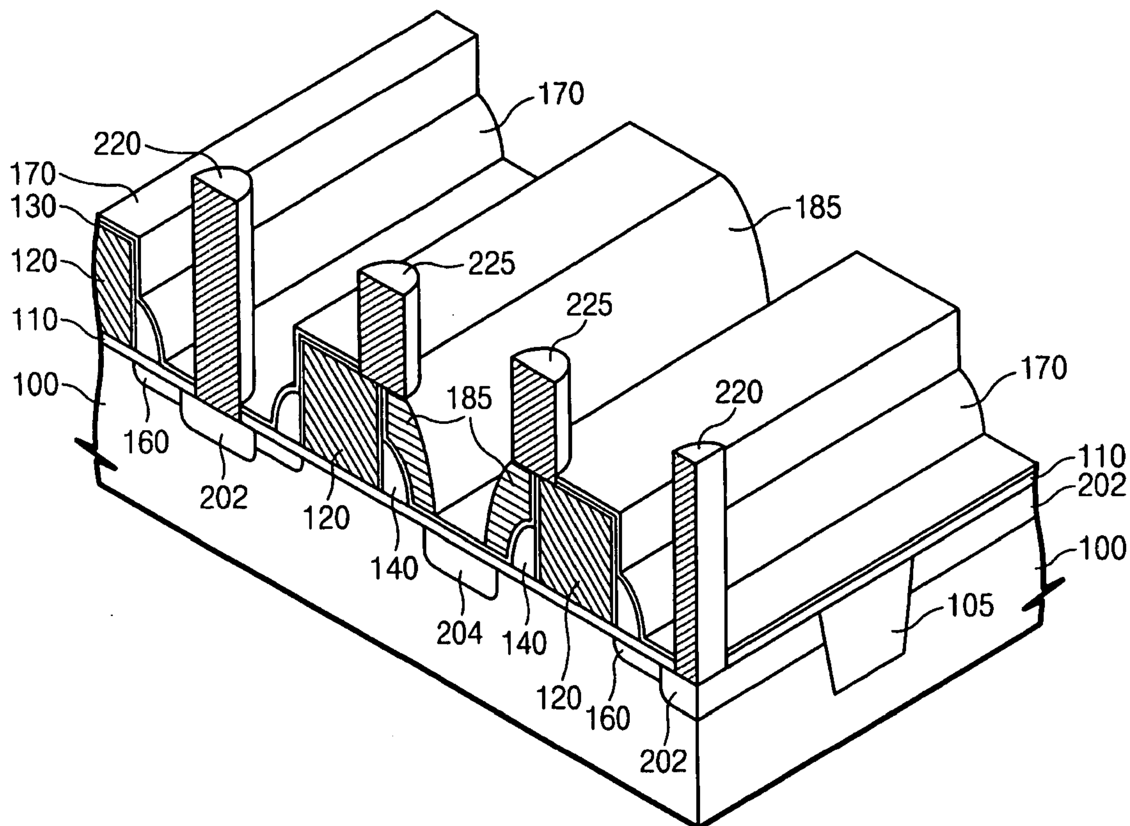


Fig. 2C

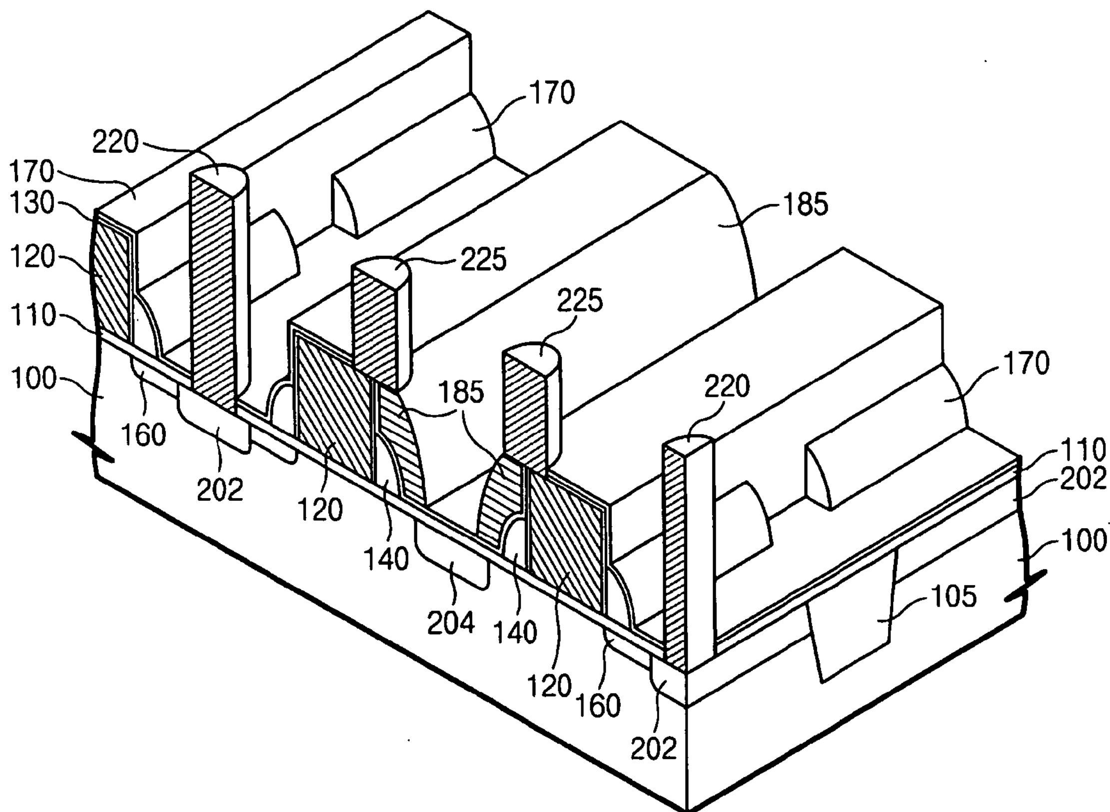


Fig. 2D

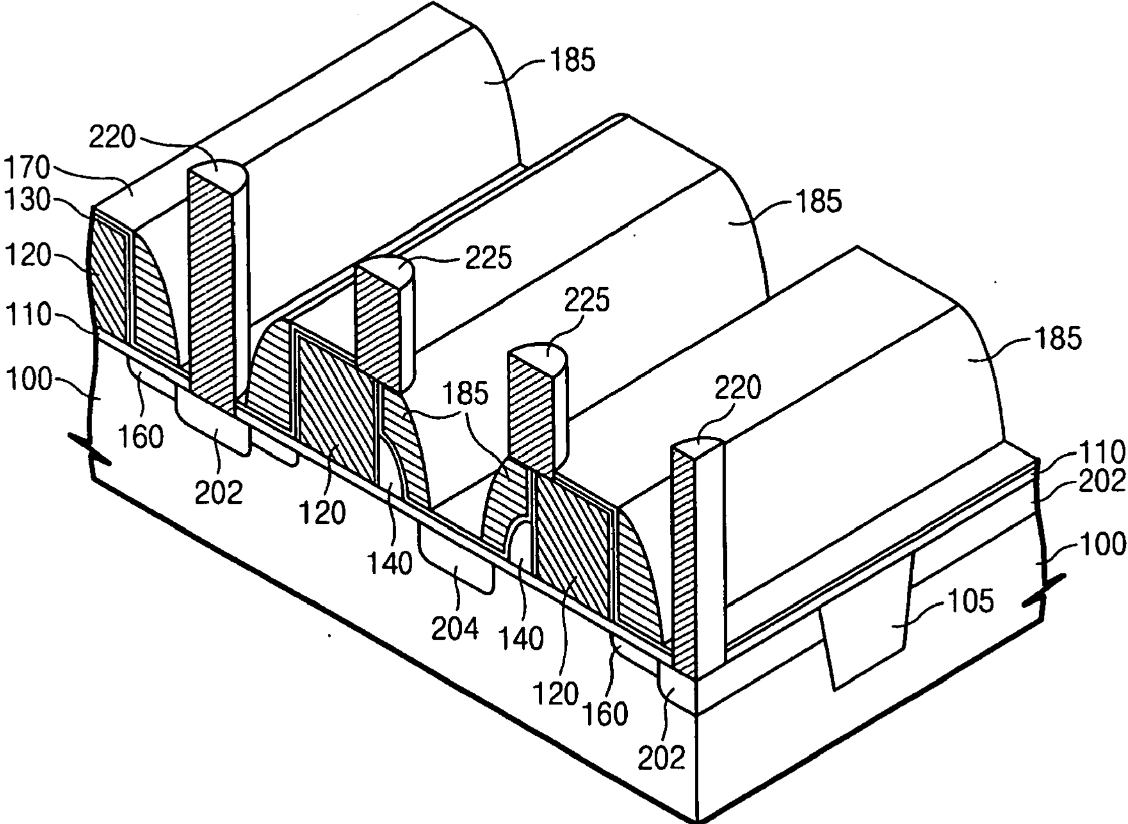


Fig. 2E

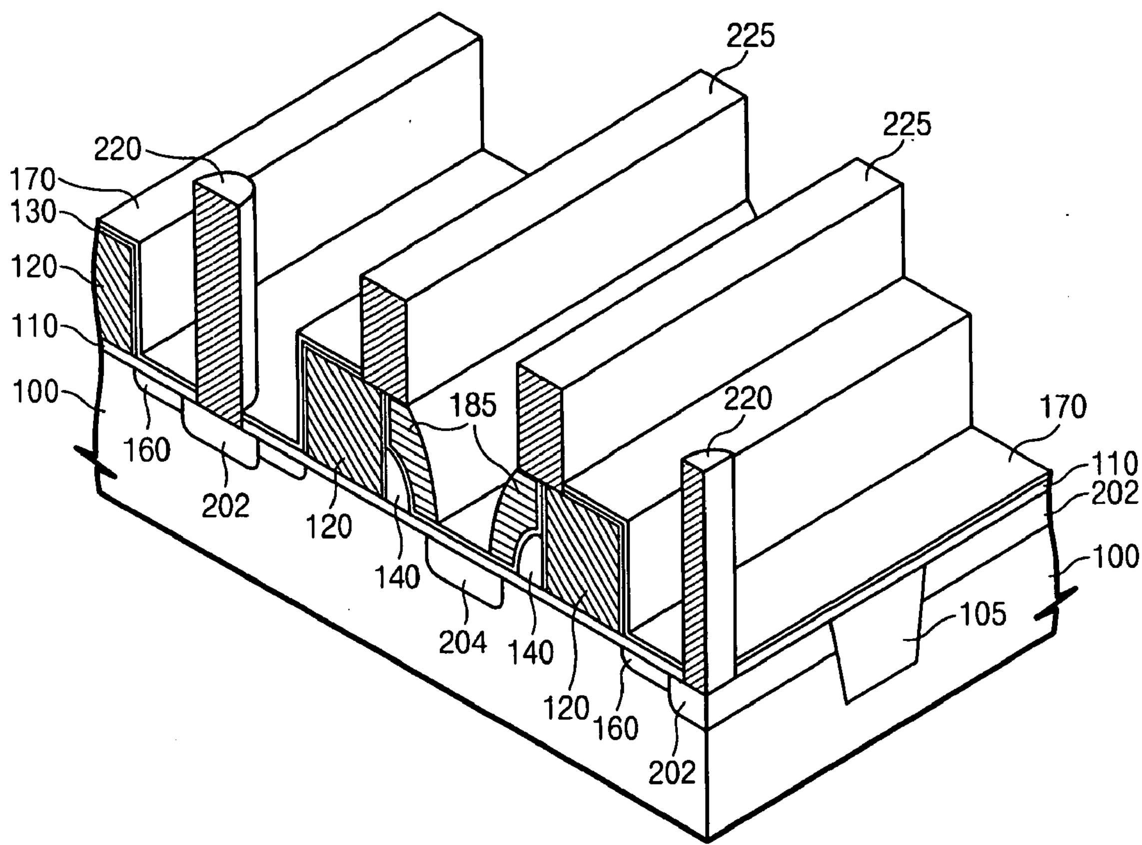


Fig. 3

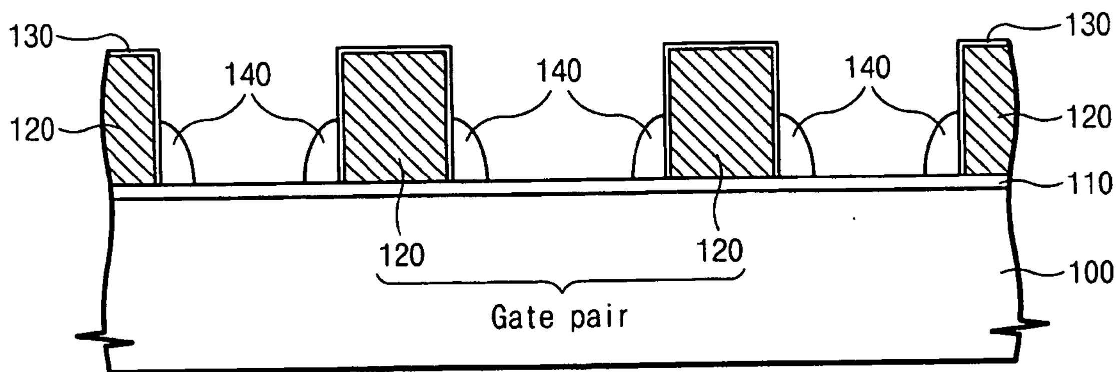


Fig. 4

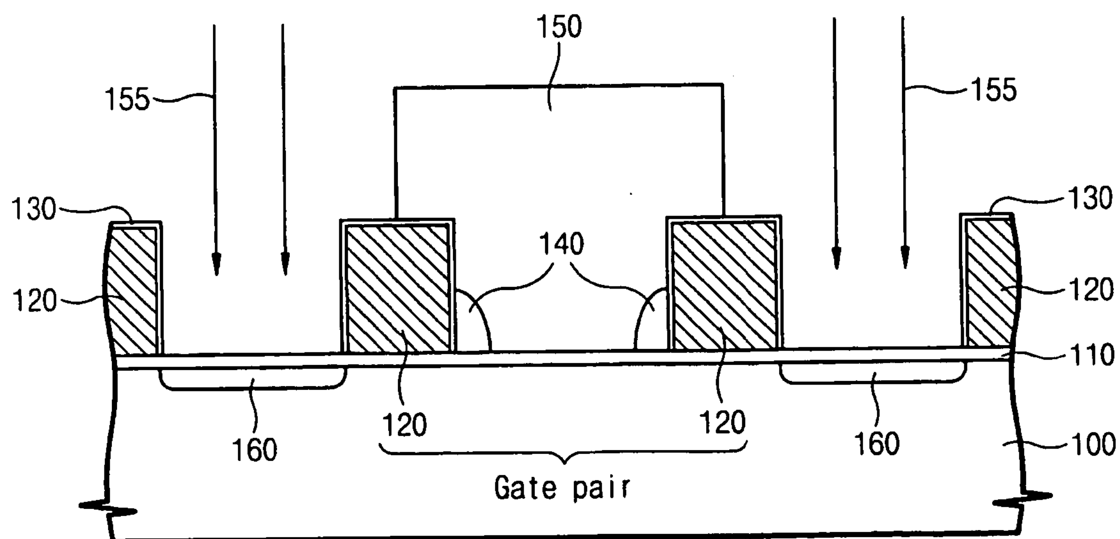


Fig. 5

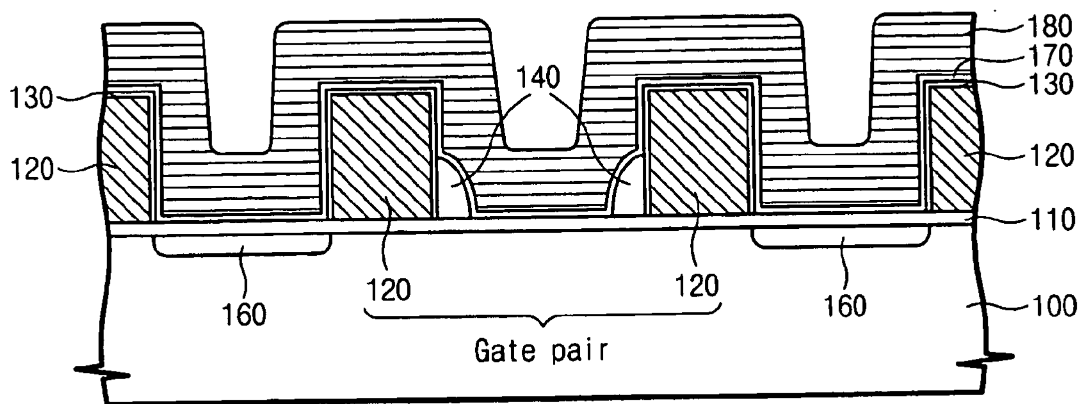


Fig. 6

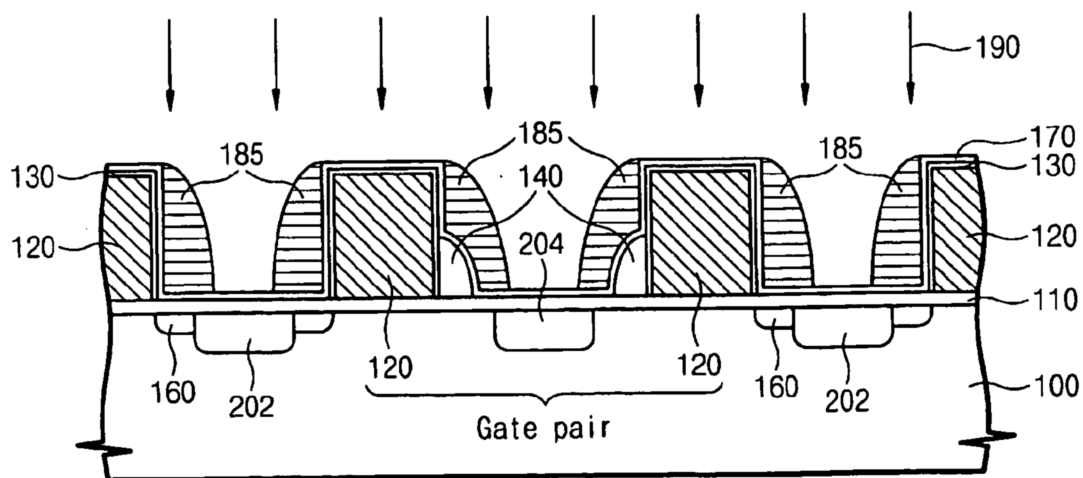


Fig. 7

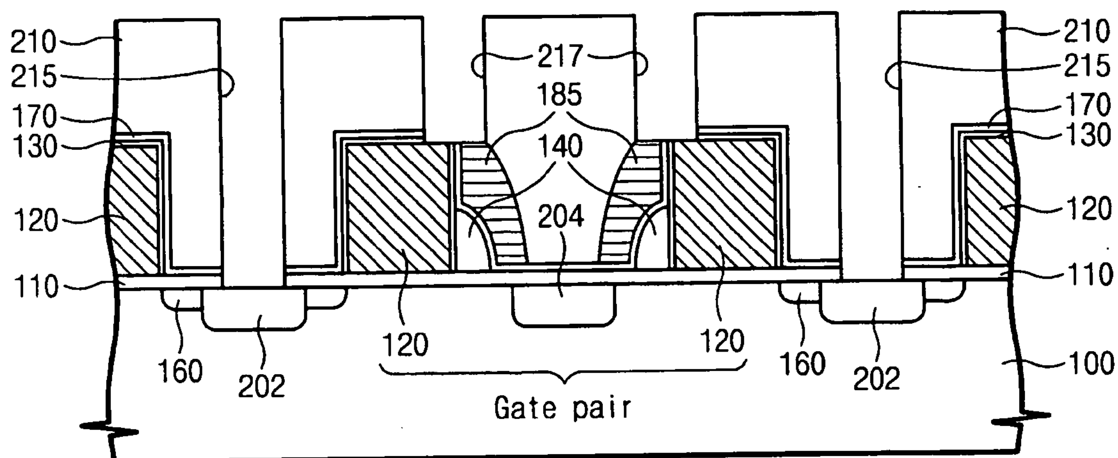


Fig. 8

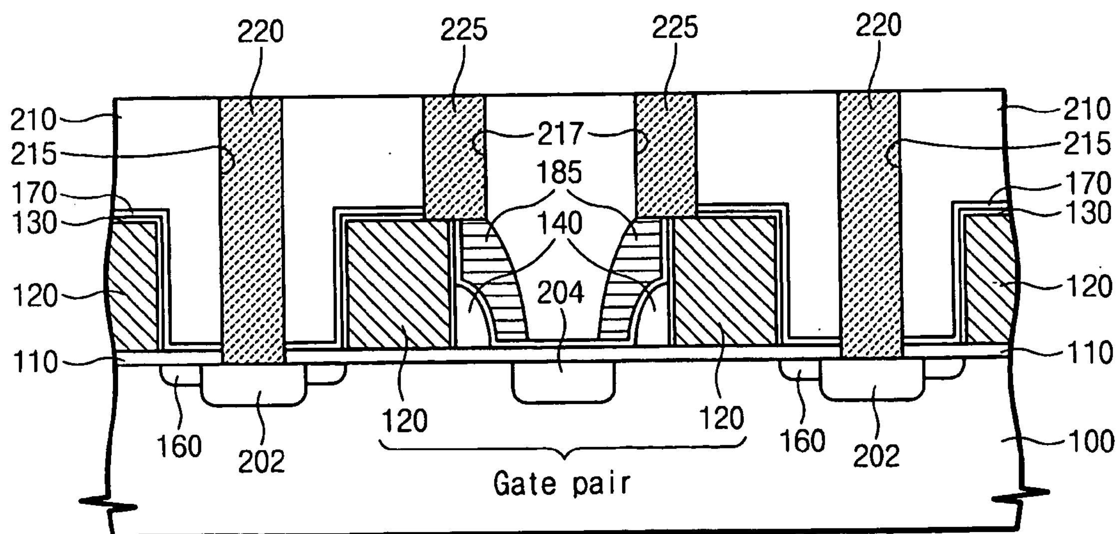


Fig. 9

(PRIOR ART)

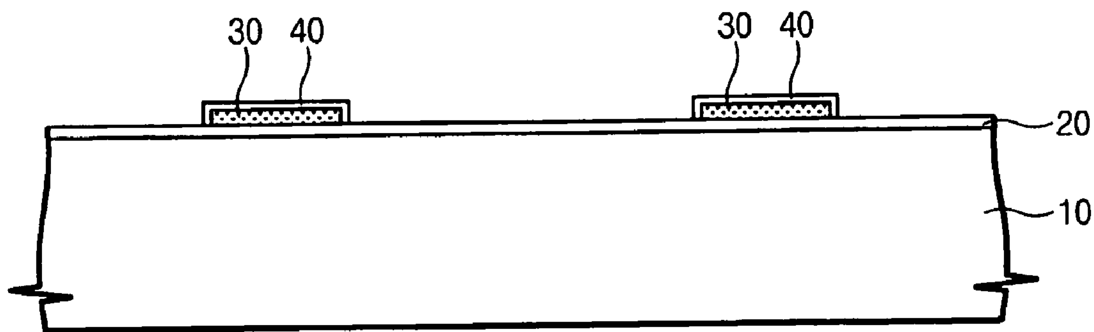
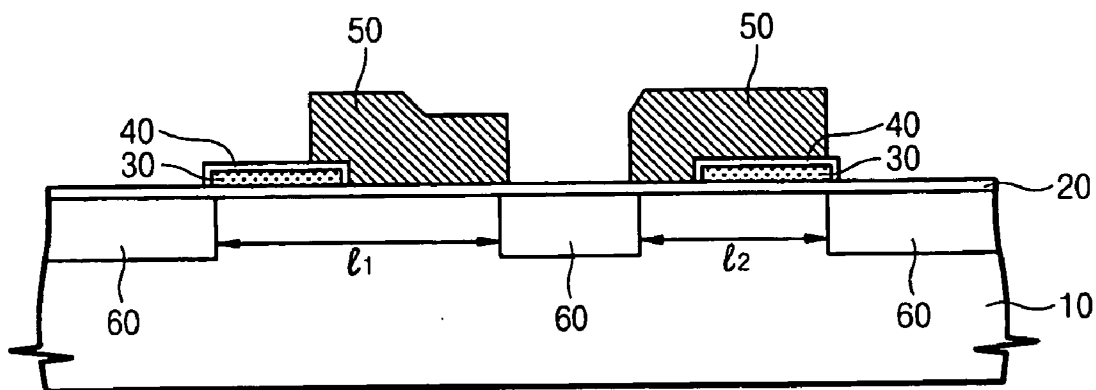


Fig. 10

(PRIOR ART)



NONVOLATILE MEMORY DEVICE AND METHOD OF FORMING SAME

[0001] This application claims the priority of U.S. patent application Ser. No. 10/761,250 (parent application), filed on Jan. 22, 2004, the disclosure of which is incorporated herein in its entirety by reference.

BACKGROUND OF THE INVENTION

[0002] 1. Field of the Invention

[0003] The present invention relates to a nonvolatile memory device and a method of forming a nonvolatile memory device.

[0004] 2. Description of Related Art

[0005] As electrical devices become miniaturized and portable, the need for nonvolatile memory devices becomes even greater. In general, nonvolatile memory devices store information without having to supply electrical power. For example, a nonvolatile memory device such as a flash memory employs a floating gate to store information. The flash memory changes information stored in a cell transistor, for example, by performing program and erase operations. The program and erase operations generally require large voltage differences (greater than about 10 volts). Accordingly, the flash memory includes a plurality of pumping circuits to establish the necessary large voltage difference. As the number of pumping circuits needed on the nonvolatile memory device rise, the integrity of a semiconductor device product containing the nonvolatile memory device is reduced, and cost of the product increases. In addition, the flash memory has a technical disadvantage, in that the transistor employing the flash memory (and interconnections thereto) should be designed so as to avoid breakdown due to the large voltage difference.

[0006] As an alternative to flash memory devices, a silicon-oxide-nitride-oxide-silicon (SONOS) type nonvolatile memory device has recently been studied and proposed. Generally, the SONOS type nonvolatile memory device includes sequentially stacked layers, e.g., an oxide layer, a nitride layer, another oxide layer and a polysilicon layer that are sequentially stacked. The nitride layer is sandwiched between the oxide layers and used as an electric charge trapping medium. Information is stored in the charge trapping medium of the SONOS type nonvolatile memory device. In other words, the nitride layer performs a function similar to the function of a floating gate in the flash memory device.

[0007] In order to provide a highly integrated semiconductor device, a SONOS type nonvolatile memory may be included in a structure where two adjoining cells, such as memory transistor cells, share a common source line. In this case, the two cells may have different channel lengths. Asymmetrical channel lengths may occur in what is referred to as a 'split-gate' type FLASH memory, for example.

[0008] **FIGS. 9 and 10** are perspective views illustrating a prior art method for fabricating a SONOS type nonvolatile memory device. Referring to **FIGS. 9 and 10**, a lower oxide layer **20** is formed on the semiconductor substrate **10**, and a charge storage pattern **30** is formed on the lower oxide layer **20**. The charge storage pattern **30** is formed of an insulating layer (such as a silicon nitride layer, for example) having a sufficient number of charge trap sites. Then, an upper oxide layer **40** is formed on the charge storage pattern **30** so as to conform to the charge storage pattern **30**.

[0009] A gate conductive layer is formed over an entire surface of the semiconductor substrate **10** and the upper oxide layer **40**. The gate conductive layer is then patterned to form gate patterns **50** crossing over the charge storage pattern **30**. An ion implantation process is performed using the gate patterns **50** as a mask to form an impurity region **60** in the semiconductor substrate **10**. The impurity regions **60** are used as a source and/or a drain of a memory cell transistor.

[0010] The gate patterns **50** are typically formed by a conventional photolithographic process so as to be misaligned to the charge storage pattern **30**. As shown in **FIG. 10**, channel lengths I1 and I2 of the adjoining two cell transistors may be changed by the misalignment between the gate pattern **50** and the charge storage pattern **30** (i.e., I1≠I2).

[0011] The asymmetry due to the misalignment may cause what is known as 'periodical irregularities' to appear at interconnections between one or more cell transistors and the one source line. These periodical irregularities are commonly known as 'even-odd failures' and may adversely affect cell transistor performance.

SUMMARY OF THE INVENTION

[0012] An exemplary embodiments of the present invention is directed to a method of forming a silicon-oxide-nitride-oxide-silicon (SONOS) type nonvolatile memory device and a SONOS type memory device. In the method, a plurality of first gates may be formed on a semiconductor substrate. A plurality of charge storage spacers may be formed on the plurality of first gates so that a given charge storage spacer may be disposed on a sidewall of a given first gate. A plurality of second gates may be disposed on the plurality of first gates so that a given second gate is on a sidewall of a given first gate and covers a given charge storage spacer.

BRIEF DESCRIPTION OF THE DRAWINGS

[0013] Exemplary embodiments of the present invention will become more fully understood from the detailed description herein below and the accompanying drawings, wherein like elements are represented by like reference numerals, which are by way of illustration only and thus do not limit the exemplary embodiments of the present invention and wherein:

[0014] **FIGS. 1A** to **1**H are top plan views illustrating a SONOS type nonvolatile memory device in accordance with the exemplary embodiments of the present invention.

[0015] **FIGS. 2A** to **2**E are perspective views illustrating a SONOS type non-volatile memory device in accordance with the exemplary embodiments of the present invention.

[0016] FIGS. **3** to **8** are perspective views illustrating a method for forming a SONOS type non-volatile memory in accordance with the exemplary embodiments of the present invention.

[0017] **FIGS. 9 and 10** are perspective views illustrating a prior art method for fabricating a SONOS type nonvolatile memory device.

DETAILED DESCRIPTION OF THE EXEMPLARY EMBODIMENTS

[0018] The present invention will be described more fully hereinafter with reference to the accompanying drawings, in which exemplary embodiments of the invention are shown. The present invention is not limited to the exemplary embodiments set forth herein, which are provided so that the disclosure will be thorough and complete, and will fully convey the scope of the invention to those skilled in the art. In the drawings, the thickness of layers and regions are exaggerated for clarity. It will also be understood that when a layer is referred to as being "on" another layer or semiconductor substrate, it can be directly on the other layer or semiconductor substrate, or intervening layers may also be present. Like numbers refer to like elements throughout.

[0019] **FIGS. 1A** to 1H are top plan views illustrating a SONOS type nonvolatile memory device, and **FIGS. 2A** to 2E are perspective views illustrating a SONOS type nonvolatile memory device in accordance with the exemplary embodiments of the present invention. **FIGS. 2A** to 2E correspond to **FIGS. 1A, 1C**, 1D, 1E and 1F, respectively.

[0020] Referring to **FIGS. 1A** to 1H and 2A to 2E, the SONOS type nonvolatile memory device may include a plurality of device isolating layers **105** disposed so as to define active regions in a given region or area of a substrate **100**. The device isolating layers **105** may be disposed along columns (i.e., x-axis) and rows (i.e., y-axis), i.e., in 2-dimensions. In this case, each device isolating layer **105** may be island-shaped so as to have a different length and width. For example, the device isolating layers **105** may be rectangular-shaped or elliptical-shaped active regions.

[0021] The SONOS type nonvolatile memory device may include a plurality of first gates **120** provided on the substrate. The first gates **120** may be arranged in parallel along columns or rows, for example. In an exemplary embodiment, several first gates **120** may be arranged so as to cross over device isolating layers **105**. That is, a plurality of device isolating layers **105** are disposed in parallel along one direction, and a plurality of first gates **120** are arranged so as to cross over these device isolating layers **105**, perpendicular to the device isolating layers **105**.

[0022] Based on the above configuration, two different first gates **120** may be arranged at sides (i.e., one first gate on either side) of an arbitrary first gate **120**. The arbitrary first gate may be referred to as a 'reference gate'. Thus may be illustrated in **FIG. 1A**, for example, where a first gate **120** labeled "Ref" at an upper portion of **FIG. 1A** may represent the reference gate, a first gate **120** is labeled "L" to the left of the first gate labeled Ref, and a first gate **120** is labeled "R" to the right of the first gate labeled Ref. The reference gate (Ref) and left gate (L) cross over the same device isolating layer **105**. The reference gate (Ref) and right gate (R) cross over different device isolating layers **105**, as shown in **FIG. 1A**, for example. The reference gate (Ref) and right gate (R) may be hereinafter referred to as a 'gate pair'. In other words, the gate pair represents adjoining first gates **120** that cross over different device isolating layers **105**.

[0023] The active region between an adjoining gates of a gate pair (i.e., L and Ref being adjoining gates of one pair; Ref and R being adjoining gates of another gate pair in **FIG. 1A**) may be referred to as a first impurity region **202**. The first impurity regions **202** may be used as a drain of the cell transistors. The first impurity regions **202** are divided by the device isolating layers **105**. Bit line contact plugs **220** may be disposed on each of the first impurity regions **202**. The bit line contact plugs **220** may be connected by a bit line (not shown). The bit line contact plugs **220** may be arranged along a direction that is perpendicular to the first gates **120**, for example.

[0024] The active regions between the gate pair may be referred to as second impurity regions **204**. The second impurity regions **204** may be used as a source region of cell transistors, for example. The first gates **120** of the gate pair cross over different device isolating layers **105** without being divided by the device isolating layers **105**. Therefore, the second impurity region **204** may be used as a common source line connecting the source regions of a plurality of transistors.

[0025] The SONOS type nonvolatile memory device may include charge storage spacers **140**. The charge storage spacers **140** may be provided on one sidewall of the first gate **120**, so as to be disposed between two first gates **120** constituting the gate pair (i.e., adjacent to the second impurity region **204**). Alternatively, as illustrated in **FIGS. 1C, 1D**, 1G, 1H, 2B and 2C, the charge storage spacers **140** may be disposed on another sidewall of the first gate **120** (i.e., adjacent to the first impurity region **202**). However, in this configuration adjacent first impurity region **202**, the charge storage spacers do not perform an information-storing function of a memory, but employed as a mask in an ion implantation process, for example.

[0026] The charge storage spacers **140** may be cut over the device isolating layer **105** to form a rectangular-shaped island, as illustrated in **FIGS. 1B, 1D**, 1H and 2C. Alternatively, instead of being cut over the device isolating layer **105**, the charge storage spacers **140** may be arranged so as to extend in a continuous fashion along a sidewall of the first gate **120**.

[0027] The SONOS type nonvolatile memory device may include second gates **185**. Two second gates **185** on a top surface and sidewalls of the charge storage spacers **140** may be disposed between the gate pair. The second gates **185** may be formed at, or in the vicinity of, a region where the charge storage spacers **140** are arranged, such that a second gate **185** covers one charge storage spacer **140**. Alternatively, a second gate **185** may be disposed at both sidewalls of a first gate **120**, as illustrated in **FIGS. 1E, 1G**, 1H and 2D, for example.

[0028] An interlayer insulating layer (not shown) may cover the semiconductor substrate, first gates **120** and second gates **185**. A connector **225** may be disposed in the interlayer insulating layer to connect the second gates **185** and first gates **120**. As illustrated in **FIGS. 1A-1E**, 1G, 1H, and 2A-2D, for example, the connector **225** may have a rod-shaped form, similar to the bit line contact plug **220**. Alternately, as illustrated in **FIGS. 1F and 2E**, the connecter **225** may be continuously disposed along the first gate **120** without being cut. The non-cut connector **225** of **FIGS. 1F and 2E** may be employed in any of the other exemplary embodiments.

[0029] The SONOS type nonvolatile memory device may include a gate insulating layer **110** that is disposed on the

semiconductor substrate **100**. The first gate **120**, second gate **185** and charge storage spacer **140** may be disposed on the gate insulating layer **110**. A first insulating layer **130**, such as a silicon oxide layer, for example, may be disposed between the first gate **120** and a second insulating layer **170**.

[**0030**] The second insulating layer **170** may be disposed between the charge storage spacer **140** and second gate **185**. Additionally, the second insulating layer **170** may be arranged so as to be between the first gate **120** and the second gate **185**, as well as between the second gate **185** and the gate insulating layer **110**. In accordance with the exemplary embodiments of the present invention, a non-volatile memory may operate (e.g., to perform operations or functions such as programming, erasing, reading, etc.), in accordance with conventional operation mechanisms such as hot carrier injection, Fowler-Nordheim tunneling, etc. Exemplary operating conditions in accordance with the exemplary embodiments of the present invention may be shown in Table 1, it being understood that the nonvolatile memory in accordance with the exemplary embodiments of the present invention may be operated under operating conditions that are different from, or a modification of, the operating conditions shown in Table 1.

TABLE 1

OPERATING CONDITIONS OF CELL TRANSISTOR

	gate	source	drain	substrate
programming	Vcc	H/V	GND	GND
erasing	H/V	0	0	0
reading	Vcc	0	Vcc/2	GND

[**0031**] Referring to Table 1, during a programming operation, a voltage Vcc may be applied to a gate electrode of the nonvolatile memory in accordance with the exemplary embodiments of the present invention. Therefore, even when a high voltage H/V is applied to the gate electrode, dissipation current may be prevented from overflowing.

[**0032**] FIGS. **3** to **8** are cross-sectional views illustrating a method for forming a SONOS type nonvolatile memory device in accordance with the exemplary embodiments of the present invention. **FIG. 3-8** illustrate sequential steps of a fabricating process for forming a SONOS type memory device. Each of **FIGS. 3-8** illustrate a cross-section as taken along a dotted line I-I' of **FIG. 1A**.

[**0033**] Referring to **FIG. 3**, and with reference to **FIG. 1A**, a plurality of device isolating layers **105** may be formed so as to define active regions in a given region or area of semiconductor substrate **100**. A gate insulating layer **110** may then be formed on the active region, and a first gate conductive layer formed on an entire surface of the semiconductor substrate **100**, including the gate insulating layer **110**.

[**0034**] As discussed above, the device isolating layers **105** may be disposed along columns in two-dimensions (i.e., x-axis direction and y-axis direction). Thus, each device isolating layer **105** may be island-shaped (rectangular-shaped or elliptical-shaped active regions, for example) so as to have a different length and width. The device isolating layer **105** may be formed using a conventional Local Oxidation of Silicon (LOCOS) technology, for example. Alternatively, trench technology may be used for forming the device isolating layer **105**. In addition, the gate insulating layer **110** may be formed of silicon oxide by thermally oxidizing the active region on semiconductor substrate **100**. The first gate conductive layer may be formed of polysilicon, or polysilicon and silicon layers that are sequentially stacked, for example. An insulating layer used as an anti-reflecting layer or a hard mask layer ("mask") may be further disposed on the first gate conductive layer.

[**0035**] Then, the first gate conductive layer is patterned to form a plurality of first gates **120** crossing over the active region and device isolating layer **105**. The first gates **120** may be disposed in parallel along columns or rows. In an exemplary embodiment, a plurality of device isolating layers **105** may be disposed in parallel along one direction, and two of the first gates **120** may be formed to cross over these parallel device isolating layers **105**. In this case, two of the first gates **120** may be embodied as the aforementioned gate pair illustrated in **FIG. 1A**. In other words, the gate pair may represent the adjoining two first gates **120** (Ref and R) crossing over the different or separate device isolating layers **105** of **FIG. 1A**.

[**0036**] A first insulating layer **130** may be formed on an entire surface of a portion of the semiconductor substrate **100** that includes the first gates **120**. For example, the first insulating layer **130** may be formed of silicon oxide by thermally oxidizing surfaces of the first gates **120**, or may be formed by a chemical vapor deposition (CVD) process, for example.

[**0037**] Continuously, a charge storage layer (not shown for reasons of clarity) may be formed so as to conform to the surface of the semiconductor substrate **100** and first insulating layer **130**. The charge storage layer is employed for storing information in a SONOS type nonvolatile memory device, for example. The charge storage layer may be formed of a material that has sufficient trap sites for storing information, such as silicon nitride or silicon oxynitride, for example, or another material that has sufficient trap sites for storing information. The charge storage layer may be anisotropically etched to form charge storage spacers **140**. The charge storage spacers **140** may be disposed on sidewalls of the first gates **120**. The charge storage spacers **140** may be formed so that top surfaces of the charge storage spacers **140** are lower than the first gates **120**, as shown in **FIG. 3**. In order to accomplish this, the anisotropic etching process is performed to expose the first insulating layer **130** on the first gate **120**, and to expose the gate insulating layer **110** on the active region between the first gates **120**. The etching process may employ an etch recipe having etch selectivity with respect to the silicon oxide layer, or with respect to a silicon layer.

[**0038**] Referring now to **FIG. 4**, with reference to **FIG. 1A**, a mask pattern **150** is formed on a given region of the semiconductor substrate **100** that includes the charge storage spacers **140**. The mask pattern **150** may be a photoresist formed by a conventional photolithographic process, for example. The mask pattern **150** is formed to cover the charge storage spacers **140** between the gate pair and the active regions between the charge storage spacers **140**. In this case, both sidewalls of the mask pattern **150** are formed in the middle of a top surface of each first gate **120**, as shown in

FIG. 4. Thus, any charge storage spacers **140** on the external sidewalls of the gate pair (see **FIG. 3**, for example) are exposed.

[**0039**] Using the mask pattern **150** as an etch mask, the exposed charge storage spacers **140** may be removed via a suitable etching process; **FIG. 4** illustrates a state of the fabrication process in which the charge storage spacers **140** on the external sidewalls of the pair of first gates **120** have already been removed. In this case, the internal charge storage spacers **140** covered with the mask pattern **150** are not etched, as shown in **FIG. 4**. The etching process may be performed using an etch recipe having etch selectivity with respect to the gate insulating layer **110**, the first insulating layer **130** and the mask pattern **150**. The etching process may be an isotropic etching or wet etching process for example, e.g., a wet etching process using an etchant with phosphoric acid, for example.

[**0040**] Using the mask pattern **150** and the first gates **120** as an etch mask, a first ion implantation process **155** may be performed to form a first impurity region **160**. The first impurity region **160** may be used as a drain of a cell transistor, and is formed in the active region between the gate pair. As illustrated in **FIGS. 1A** to 1H, the first impurity region **160** is divided by the device isolating layers **105**.

[**0041**] The charge storage spacers **140** covered with the mask pattern **150** between the pair of gates are thus not removed (See **FIGS. 1C, 1D**, 1G and 1H). In this case, the first impurity region **160** is spaced apart from the charge storage spacers **140** by first gates **120**. However, the first impurity region **160** may be expanded during subsequent processes so as to extend under the charge storage spacers **140**. This may be accomplished using thermal diffusion, for example.

[**0042**] Referring now to **FIG. 5**, and with reference to **FIG. 1A**, the mask pattern **150** may be removed to expose the charge storage spacers **140**. A second insulating layer **170** and a second gate conductive layer **180** may then be sequentially formed on the entire surface of the semiconductor substrate **100**, once the mask pattern **150** has been removed.

[**0043**] The second insulating layer **170** may be formed of silicon oxide by a CVD process, for example, so as to have good step coverage. Operation of the nonvolatile memory could be substantially affected by the thickness of the second insulating layer **170**. Thus, the second insulating layer **170** may be formed by an atomic layer deposition (ALD) process to more precisely control deposition thickness.

[**0044**] The second gate conductive layer **180** may be formed of polysilicon so as to have good step coverage. For example, the second gate conductive layer **180** may be formed by a CVD process that includes a step of thermally dissolving the polysilicon with silane gas (SiH_4) or disilane gas (Si_2H_6). In addition, the step of forming the second gate conductive layer **180** may further include performing an impurity doping step, either by ion-implantation or in-situ, in order to ensure that the second gate conductive layer **180** has good conductivity characteristics. Referring now to **FIG. 6**, and with reference to **FIG. 1A**, the second gate conductive layer **180** may be anisotropically etched until the second insulating layer **170** is exposed to thereby form the second gates **185**. The second gates **185** may be disposed on both sidewalls of the first gates **120**, as shown in **FIG. 6** for example.

[**0045**] Referring now to **FIG. 8**, the second gates **185** disposed in facing relation on internal sidewalls of the gate pair may serve as another gate electrode of the SONOS type nonvolatile memory. As shown in **FIG. 8**, the second gate **185** may be connected to the adjoining first gates **120**. Meanwhile, and as shown in **FIG. 6**, the portions of the second gates **185** that are disposed on external sidewalls of the gate pair do not serve as a gate electrode, but may be used as an ion implantation mask in a subsequent process, for example.

[**0046**] A second ion implantation process **190** may be performed using the second gates **185** and first gates **120** as a mask. Thus, the second impurity region **204** may be formed in the active region between the first gates **120** composing the gate pair. The second impurity region **204** may be used as a source of a cell transistor. Additionally, a high-concentration drain region **202**, which may be used as a drain of the cell transistor, may also be formed by the second ion implantation process **190** in the first impurity region **160**, i.e., the active region between the gate pair.

[**0047**] In order to improve efficiency of a programming operation, the impurity concentration in the second impurity region **204** should be higher than the impurity concentration in the high-concentration drain region **202**. Therefore, after forming another mask pattern to screen the first impurity region **160**, an additional ion implantation process may be performed to inject impurities into the second impurity region **204**.

[**0048**] Referring to **FIG. 4** and **FIG. 6**, and according to an exemplary embodiment where the charge storage spacer **140** on external sidewalls of the first gates **120** have been removed, concentrations of the first ion implantation process **155** and second ion implantation process **190** may be different. Accordingly, the concentrations of the high-concentration drain region **202** and the second impurity region **204** may have different concentrations.

[**0049**] Referring now to **FIG. 7**, an interlayer insulating layer **210** may be formed on an entire surface of the semiconductor substrate **100**, including the second impurity region **204**. The interlayer insulating layer **210** may be patterned to form a contact hole **215** exposing the high-concentration drain region **202**. A contact hole **215** may also be formed to expose the second impurity region **204** at a given region or area (not shown).

[**0050**] The interlayer insulating layer **210** may be composed of silicon oxide, silicon nitride or silicon oxynitride, for example. In addition, the interlayer insulating layer **210** may be formed by a CVD process, by a spin coating process, or by a physical vapor deposition (PVD) process, for example.

[**0051**] To form the interlayer insulating layer **210**, as illustrated in **FIG. 7**, selected second gates **185** may be selectively removed. An etch mask exposes those second gates **185** disposed on first impurity region **160** for the selective removal of certain second gates **185**. Thus, the mask pattern **150** used for forming the first impurity region **160** may be re-formed and used as an etching mask for the selective removal of certain second gates **185**. The selective removal may be performed using an etch recipe having an etch selectivity with respect to the interlayer insulating layer **200** such as a silicon oxide layer. In addition, the selective

removal may be performed by an isotropic etching process such as wet etching, for example. A resultant structure, where the second gates **185** have been selectively removed, has a plan structure as illustrated in **FIGS. 1A, 1B**, 1C, 1D and 1F. Alternatively, as illustrated in **FIGS. 1E, 1G** and 1H, an interlayer insulating layer **210** may be formed without removing the second gates **185**.

[**0052**] In forming the contact hole **215**, a connection opening **217** may be formed to expose the first gate **120** and second gate **185** adjacent to the first gate **120**, as shown in **FIG. 7**, for example. The connection opening **217** may be a hole type opening (such as the contact hole **215**) or a groove type opening that is not cut in the middle, as illustrated in **FIG. 1F**, for example.

[**0053**] Referring now to **FIG. 8** and with occasional reference to **FIG. 1A**, a plug conductive layer may be formed on an entire surface of the semiconductor substrate **100** to fill the contact hole **215** and connection opening **217**. The plug conductive layer may be etched to expose a top surface of the interlayer insulating layer **210**, thereby forming a contact plug **220** that fills contact holes **215**, and a connector **225** that fills the connection openings **217**, respectively.

[**0054**] The plug conductive layer may be composed of a material selected from a group consisting of polysilicon, aluminum, tungsten, titanium, titanium nitride, tantalum and tantalum nitride, for example. The connector **225** electrically connects the first gate **120** and the adjoining second gate **185**. Meanwhile, the etching of the plug conductive layer may be performed using a chemical mechanical polishing (CMP) process. In addition, the plug conductive layer may be over etched so as to be lower than a top surface of the interlayer insulating layer **210**. Thus, the top of the contact plug **220** and the top of the connector **225** may be lower than a top surface of the interlayer insulating layer **210**. Afterwards, another interlayer insulating layer may be formed on an entire surface of the resultant structures to form a bit line to connect the contact plugs **220**.

[**0055**] According to the exemplary embodiments of the present invention, a gate electrode of a nonvolatile memory device of a cell transistor may be formed by a process used for forming charge storage spacers that store information in the nonvolatile memory device. The gate electrode may configured so as to be self-aligned to the charge storage spacers, potentially preventing even-odd failure. In addition, a photolithographic process is not required in order to form the second gate electrode, so that production costs can be reduced. Accordingly, a stable SONOS type nonvolatile memory device may be fabricated at low cost. In addition, a voltage Vcc may be applied to a gate electrode during programming in an effort to prevent current from overflowing. Thus, a SONOS type nonvolatile memory device may be fabricated so as to have low or substantially low power consumption.

[**0056**] The exemplary embodiments of the present invention being thus described, it will be obvious that the same may be varied in many ways. Such variations are not to be regarded as departure from the spirit and scope of the exemplary embodiments of the present invention, and all such modifications as would be obvious to one skilled in the art are intended to be included within the scope of the following claims.

1.-**14**. (canceled)

15. A silicon-oxide-nitride-oxide-silicon (SONOS) type nonvolatile memory device, comprising:

a plurality of first gates disposed on a given region of a semiconductor substrate;

a plurality of charge storage spacers disposed on the plurality of first gates so that a given charge storage spacer is on a sidewall of a given first gate; and

a plurality of second gates disposed on the plurality of first gates so that a given second gate is on a sidewall of a given first gate and covers a given charge storage spacer.

16. The device of claim 15, further comprising:

a plurality of device isolating layers defining an active region disposed in a given region of the semiconductor substrate, wherein the device isolating layers are two-dimensionally disposed along columns and rows.

17. The device of claim 16, wherein

the plurality of first gates cross over the plurality of device isolating layers and are parallel to each other, and

a given pair of first gates are disposed on each of the device isolating layers.

18. The device of claim 17, wherein

the charge storage spacers are disposed on internal sidewalls of an adjoining two first gates, and

each first gate of the adjoining two first gates crosses over a different device isolating layer.

19. The device of claim 18, further comprising:

an impurity region disposed between a given pair of charge storage spacers that are disposed on the internal sidewalls of the adjoining two first gates, wherein the impurity region represents a common source line of adjoining cell transistors.

20. The device of claim 17, further comprising:

an impurity region disposed between a given pair of first gates crossing over the same device isolating layer, wherein the impurity region is divided by the device isolating layer.

21. The device of claim 20, further comprising:

a plurality of insulating spacers disposed adjacent to the impurity region, each insulating spacer disposed on another sidewall of a given first gate opposite to the sidewall on which a given charge storage spacer is disposed.

22. The device of claim 20, further comprising:

a material pattern disposed adjacent to the impurity region and on another sidewall of a given first gate opposite to the sidewall on which a given charge storage spacer is disposed, wherein the material pattern is formed of an material substantially identical to a material of the second gate.

23. The device of claim 15, wherein the first gates and second gates are composed of at least one material selected from a group comprising polysilicon, silicide and metal.

24. The device of claim 15, wherein the plurality of charge storage spacers are formed of silicon nitride or silicon oxynitride.

25. The device of claim 16, wherein each of the charge storage spacers includes a sidewall that is formed on a device isolating layer to isolate a charge storage spacer from another charge storage spacer.

26. The device of claim 15, further comprising:

a gate insulating layer interposed between the first gates, second gates, charge storage spacers and semiconductor substrate;

a first insulating layer interposed between the plurality of first gates and the plurality of charge storage spacers;

a second insulating layer interposed between the plurality of charge storage spacers and the plurality of second gates; and

a connector connecting the first gates and second gates, wherein the gate insulating layer and the first insulating layer are composed of silicon oxide.

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